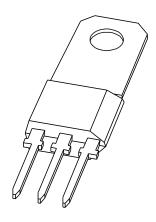
#### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## BF870; BF872 PNP high-voltage transistors

Product specification Supersedes data of September 1994 File under Discrete Semiconductors, SC04 1996 Dec 09





## PNP high-voltage transistors

BF870; BF872

#### **FEATURES**

• Low feedback capacitance.

#### **APPLICATIONS**

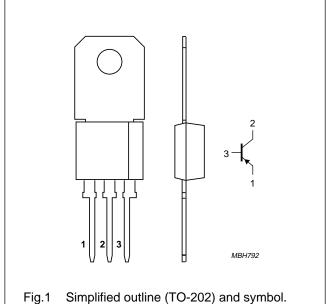
• For use in class-B video output stages of colour television receivers.

#### **DESCRIPTION**

PNP transistors in a TO-202 plastic package. NPN complements: BF869 and BF871.

#### **PINNING**

PIN	DESCRIPTION	
1	emitter	
2	collector, connected to mounting base	
3	base	



#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BF870		_	-250	V
	BF872		_	-300	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BF870		_	-250	V
	BF872		_	-300	V
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	_	5	W
h <sub>FE</sub>	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	50	_	
C <sub>re</sub>	feedback capacitance	$I_C = I_c = 0$ ; $V_{CE} = -30 \text{ V}$ ; $f = 1\text{MHz}$	_	2.2	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; f = 100 \text{ MHz}$	60	_	MHz

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BF870		_	-250	V
	BF872		_	-300	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BF870		_	-250	V
	BF872		_	-300	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-50	nA
I <sub>CM</sub>	peak collector current		_	-100	mA
I <sub>BM</sub>	peak base current		_	-50	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	1.6	W
		T <sub>mb</sub> ≤ 25 °C	_	5	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient		K/W	
R <sub>th j-mb</sub>	thermal resistance from junction to mounting base		K/W	

#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -200 V	_	-10	nA
		$I_E = 0$ ; $V_{CB} = -200 \text{ V}$ ; $T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I <sub>EBO</sub>	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-50	nA
h <sub>FE</sub>	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}$	50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -30 \text{ mA}; I_B = -5 \text{ mA}$	_	-600	mV
C <sub>re</sub>	feedback capacitance	$I_C = i_c = 0$ ; $V_{CE} = -30 \text{ V}$ ; $f = 1\text{MHz}$	_	2.2	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; f = 100 \text{ MHz}$	60	_	MHz

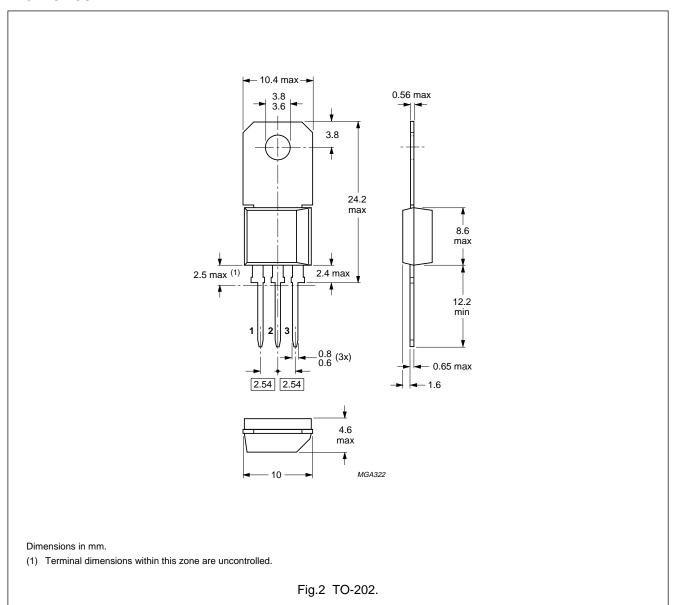
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#### **PACKAGE OUTLINE**



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#### PNP high-voltage transistors

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#### **DEFINITIONS**

Data sheet status		
Objective specification This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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